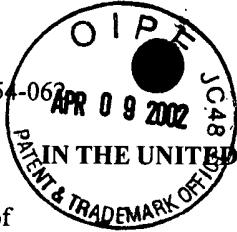


Docket No.: 57454-062



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Tomohide TERASHIMA

Serial No.: 09/834,954

: Group Art Unit: 2826

Filed: April 16, 2001

: Examiner: Johannes P. Mondt

For: SEMICONDUCTOR DEVICE

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

No additional fee is required.
Applicant is entitled to small entity status under 37 CFR 1.27
Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	12	20	0	\$18.00 =	\$0.00
Independent Claims	2	3	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
Total of Above Calculations					\$0.00

Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

Scott D. Paul
Registration No. 42,984

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Date: April 9, 2002

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PATENT

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Tomohide TERASHIMA :
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AMENDMENT

Box Non-Fee Amendment
The Commissioner for Patents and Trademarks
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated January 9, 2002. Please amend the above-identified application as follows:

IN THE CLAIMS:

Sub B
AI

1. (Amended) A semiconductor device including:
a semiconductor substrate having a main surface;
a semiconductor layer of a first conductive type which is formed on the main surface of
said semiconductor substrate;
a first buried impurity region of the first conductive type formed between said
semiconductor layer and said semiconductor substrate;